

Hai Lu

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

135
papers

1,825
citations

22
h-index

37
g-index

147
ext. papers

2,384
ext. citations

4.1
avg, IF

4.67
L-index

#	Paper	IF	Citations
135	Near-infrared ITO-based photonic hypercrystals with large angle-insensitive bandgaps.. <i>Optics Letters</i> , 2022 , 47, 917-920	3	4
134	1.2 kV/25 A Normally off P-N Junction/AlGaIn/GaN HEMTs With Nanosecond Switching Characteristics and Robust Overvoltage Capability. <i>IEEE Transactions on Power Electronics</i> , 2022 , 37, 26-30 ²	7.2	3
133	70- μ m-Body Ga ₂ O ₃ Schottky Barrier Diode with 1.48 K/W Thermal Resistance, 59 A Surge Current and 98.9% Conversion Efficiency. <i>IEEE Electron Device Letters</i> , 2022 , 1-1	4.4	2
132	M-Plane Ga ₂ O ₃ Solar-Blind Detector With Record-High Responsivity-Bandwidth Product and High-Temperature Operation Capability. <i>IEEE Electron Device Letters</i> , 2022 , 43, 541-544	4.4	2
131	3-D Simulation Study of a Normally-OFF GaN Lateral Multi-Channel JFET With Optimized Electrical Field Transfer Terminal Structure. <i>IEEE Transactions on Electron Devices</i> , 2022 , 69, 1918-1923	2.9	
130	4H-SiC n-i-p extreme ultraviolet detector with gradient doping-induced surface junction. <i>IEEE Electron Device Letters</i> , 2022 , 1-1	4.4	0
129	1000-W Resistive Energy Dissipating Capability Against Inductive Transients Demonstrated in Non-Avalanche AlGaIn/GaN Schottky Diode. <i>IEEE Electron Device Letters</i> , 2021 , 42, 1743-1746	4.4	0
128	Over 1200 V Normally-OFF p-NiO gated AlGaIn/GaN HEMTs on Si with a Small Threshold Voltage Shift. <i>IEEE Electron Device Letters</i> , 2021 , 1-1	4.4	2
127	Band evolution and Landau-Zener Bloch oscillations in strained photonic rhombic lattices. <i>Optics Express</i> , 2021 , 29, 37503-37514	3.3	0
126	Low-Voltage p-i-n GaN-Based Alpha-Particle Detector With High Energy Resolution. <i>IEEE Electron Device Letters</i> , 2021 , 1-1	4.4	1
125	Using a Modified Turian-Yuan Model to Enhance Heterogeneous Resistance in Municipal Sludge Transportation Pipeline. <i>ACS Omega</i> , 2021 , 6, 7199-7211	3.9	0
124	Quasiperiodic metamaterials empowered non-metallic broadband optical absorbers. <i>Optics Express</i> , 2021 , 29, 13576-13589	3.3	1
123	Progress on AlGaIn-based solar-blind ultraviolet photodetectors and focal plane arrays. <i>Light: Science and Applications</i> , 2021 , 10, 94	16.7	51
122	High Performance Quasi-Vertical GaN Junction Barrier Schottky Diode with Zero Reverse Recovery and Rugged Avalanche Capability 2021 ,		4
121	Nonreciprocal Tamm plasmon absorber based on lossy epsilon-near-zero materials. <i>Optics Express</i> , 2021 , 29, 17736-17745	3.3	4
120	A High Quantum Efficiency Narrow-Band UV-B AlGaIn p-i-n Photodiode With Polarization Assistance. <i>IEEE Photonics Journal</i> , 2021 , 13, 1-8	1.8	1
119	High-Voltage Quasi-Vertical GaN Junction Barrier Schottky Diode With Fast Switching Characteristics. <i>IEEE Electron Device Letters</i> , 2021 , 42, 974-977	4.4	13

118	Sustainable Application of ZIF-8 for Heavy-Metal Removal in Aqueous Solutions. <i>Sustainability</i> , 2021 , 13, 984	3.6	13
117	Sustainable Solar Evaporation while Salt Accumulation. <i>ACS Applied Materials & Interfaces</i> , 2021 , 13, 4935-4942	9.5	17
116	46.4: Fabrication of InGaN/GaN-based nano-LEDs for display applications. <i>Digest of Technical Papers SID International Symposium</i> , 2021 , 52, 568-568	0.5	
115	The generating and modulating characteristics of bound states in the continuum for both TE and TM polarizations by one-dimensional photonic crystal slabs. <i>Journal of Optics (United Kingdom)</i> , 2021 , 23, 105202	1.7	
114	VT Shift and Recovery Mechanisms of p-GaN Gate HEMTs Under DC/AC Gate Stress Investigated by Fast Sweeping Characterization. <i>IEEE Electron Device Letters</i> , 2021 , 42, 1508-1511	4.4	8
113	Demonstration of Avalanche and Surge Current Robustness in GaN Junction Barrier Schottky Diode With 600-V/10-A Switching Capability. <i>IEEE Transactions on Power Electronics</i> , 2021 , 36, 12163-12167	7.2	6
112	An Ultraviolet Photon Counting Imaging System Based on a SiC SPAD Array. <i>IEEE Photonics Technology Letters</i> , 2021 , 33, 1213-1216	2.2	
111	1.37 kV/12 A NiO/EGa ₂ O ₃ Heterojunction Diode With Nanosecond Reverse Recovery and Rugged Surge-Current Capability. <i>IEEE Transactions on Power Electronics</i> , 2021 , 36, 12213-12217	7.2	19
110	1.95-kV Beveled-Mesa NiO/EGa ₂ O ₃ Heterojunction Diode With 98.5% Conversion Efficiency and Over Million-Times Overvoltage Ruggedness. <i>IEEE Transactions on Power Electronics</i> , 2021 , 1-1	7.2	13
109	Synthesis and Properties of InGaN/GaN Multiple Quantum Well Nanowires on Si (111) by Molecular Beam Epitaxy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020 , 217, 2070028	1.6	
108	AlGaN Promising Candidate for High-Electron-Mobility Transistors. <i>IEEE Electron Device Letters</i> , 2020 , 1-1	4.4	4
107	High-Performance 4H-SiC Schottky Photodiode With Semitransparent Grid-Electrode for EUV Detection. <i>IEEE Photonics Technology Letters</i> , 2020 , 32, 791-794	2.2	4
106	After-Pulse Characterizations of Geiger-Mode 4H-SiC Avalanche Photodiodes. <i>IEEE Photonics Technology Letters</i> , 2020 , 32, 706-709	2.2	1
105	Observation of quincunx-shaped and dipole-like flatband states in photonic rhombic lattices without band-touching. <i>APL Photonics</i> , 2020 , 5, 016107	5.2	10
104	Do all screw dislocations cause leakage in GaN-based devices?. <i>Applied Physics Letters</i> , 2020 , 116, 062104	3.4	19
103	Azimuthal illumination enabled ultra-high polar angle sensitivity by a Bloch surface wave resonance refractive index sensor. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 215401	3	
102	Highly Enhanced Inductive Current Sustaining Capability and Avalanche Ruggedness in GaN p-i-n Diodes With Shallow Bevel Termination. <i>IEEE Electron Device Letters</i> , 2020 , 41, 469-472	4.4	7
101	Hybrid Light Emitters and UV Solar-Blind Avalanche Photodiodes based on III-Nitride Semiconductors. <i>Advanced Materials</i> , 2020 , 32, e1904354	24	11

100	Property manipulation through pulsed laser annealing in high dose Mg-implanted GaN. <i>Journal of Applied Physics</i> , 2020 , 128, 235704	2.5	1
99	Synthesis and Properties of InGaN/GaN Multiple Quantum Well Nanowires on Si (111) by Molecular Beam Epitaxy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020 , 217, 1900729	1.6	3
98	Electronic properties of arsenene nanoribbons for FET application. <i>Optical and Quantum Electronics</i> , 2020 , 52, 1	2.4	0
97	Plasmonic interference lithography by coupling the bulk plasmon polariton mode and the waveguide mode. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 135103	3	4
96	High- κ HfO ₂ -Based AlGaIn/GaN MIS-HEMTs With Y ₂ O ₃ Interfacial Layer for High Gate Controllability and Interface Quality. <i>IEEE Journal of the Electron Devices Society</i> , 2020 , 8, 15-19	2.3	7
95	Content and health risk assessment of heavy metals and polybrominated diphenyl ethers in fish from Songhua Lake (Jilin City), China. <i>Environmental Science and Pollution Research</i> , 2020 , 27, 40848-40856	5.1	1
94	Different I_V Behaviors and Leakage Current Mechanisms in AlGaIn Solar-Blind Ultraviolet Avalanche Photodiodes. <i>ACS Applied Electronic Materials</i> , 2020 , 2, 2716-2720	4	1
93	Second-harmonic generation from 2D photonic crystal waveguide with simultaneous near-flat dispersions at fundamental frequency and second harmonic. <i>Optics Communications</i> , 2020 , 472, 125885	2	1
92	Gate Reliability of p-GaN Gate AlGaIn/GaN High Electron Mobility Transistors. <i>IEEE Electron Device Letters</i> , 2019 , 40, 379-382	4.4	16
91	The Generalized Analytical Expression for the Resonance Frequencies of Plasmonic Nanoresonators Composed of Folded Rectangular Geometries. <i>Scientific Reports</i> , 2019 , 9, 52	4.9	2
90	Performance Modulation for Back-Illuminated AlGaIn Ultraviolet Avalanche Photodiodes Based on Multiplication Scaling. <i>IEEE Photonics Journal</i> , 2019 , 11, 1-7	1.8	4
89	Realization of p-type gallium nitride by magnesium ion implantation for vertical power devices. <i>Scientific Reports</i> , 2019 , 9, 8796	4.9	18
88	Performance of Monolayer Blue Phosphorene Double-Gate MOSFETs from the First Principles. <i>ACS Applied Materials & Interfaces</i> , 2019 , 11, 20956-20964	9.5	22
87	Investigation on the Activation Energy of Device Degradation and Switching Time in AlGaIn/GaN HEMTs for High-Frequency Application. <i>IEEE Journal of the Electron Devices Society</i> , 2019 , 1-1	2.3	0
86	Spatial Non-Uniform Hot Carrier Luminescence From 4H-SiC p-i-n Avalanche Photodiodes. <i>IEEE Photonics Technology Letters</i> , 2019 , 31, 447-450	2.2	6
85	Br doped porous bismuth oxychloride micro-sheets with rich oxygen vacancies and dominating {0 0 1} facets for enhanced nitrogen photo-fixation performances. <i>Journal of Colloid and Interface Science</i> , 2019 , 556, 111-119	9.3	39
84	Precise Extraction of Dynamic R _{dson} Under High Frequency and High Voltage by a Double-Diode-Isolation Method. <i>IEEE Journal of the Electron Devices Society</i> , 2019 , 1-1	2.3	5
83	Janus Ga ₂ SeTe: A Promising Candidate for Highly Efficient Solar Cells. <i>Solar Rrl</i> , 2019 , 3, 1900321	7.1	5

82	Effect of Very High-Fluence Proton Radiation on 6H-SiC Photoconductive Proton Detectors. <i>IEEE Electron Device Letters</i> , 2019 , 40, 1929-1932	4.4	6
81	Observation and Modeling of Leakage Current in AlGaIn Ultraviolet Light Emitting Diodes. <i>IEEE Photonics Technology Letters</i> , 2019 , 31, 1697-1700	2.2	2
80	Effects of dissipative substrate on the performances of enhancement mode AlInN/GaN HEMTs. <i>International Journal of Numerical Modelling: Electronic Networks, Devices and Fields</i> , 2019 , 32, e2482	1	3
79	Carbonized Bamboos as Excellent 3D Solar Vapor-Generation Devices. <i>Advanced Materials Technologies</i> , 2019 , 4, 1800593	6.8	68
78	Low emissivity double sides antireflection coatings for silicon wafer at infrared region. <i>Journal of Alloys and Compounds</i> , 2018 , 742, 729-735	5.7	6
77	Vertical 4H-SiC n-i-p-n APDs With Partial Trench Isolation. <i>IEEE Photonics Technology Letters</i> , 2018 , 30, 805-808	2.2	6
76	A Reusable and High Sensitivity Nitrogen Dioxide Sensor Based on Monolayer SnSe. <i>IEEE Electron Device Letters</i> , 2018 , 39, 599-602	4.4	27
75	Noise Characterization of Geiger-Mode 4H-SiC Avalanche Photodiodes for Ultraviolet Single-Photon Detection. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2018 , 24, 1-5	3.8	4
74	Guided Bloch surface wave resonance by near normal and near in-plane illuminations: the hyper azimuthal sensitivity. <i>Optics Express</i> , 2018 , 26, 12769-12778	3.3	4
73	Improving the sensitivity of compound waveguide grating biosensor via modulated wavevector. <i>Applied Physics Express</i> , 2018 , 11, 082202	2.4	9
72	High Sensitive pH Sensor Based on AlInN/GaN Heterostructure Transistor. <i>Sensors</i> , 2018 , 18,	3.8	11
71	Numerical study of the defect adamantine compound CuGaGeSe ₄ . <i>Molecular Physics</i> , 2018 , 116, 1551-1557		
70	Effective suppression of the high temperature DC performance degradation of AlInN/GaN HEMTs by back barrier. <i>International Journal of Numerical Modelling: Electronic Networks, Devices and Fields</i> , 2018 , 31, e2299	1	1
69	Effects of the Trap Level in the Unintentionally Doped GaN Buffer Layer on Optimized p-GaN Gate AlGaIn/GaN HEMTs. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018 , 215, 1700368	1.6	4
68	An ultra-sensitive and selective nitrogen dioxide sensor based on a novel PC monolayer from a theoretical perspective. <i>Nanoscale</i> , 2018 , 10, 21936-21943	7.7	19
67	Enhanced Diffuse Reflectance and Microstructure Properties of Hybrid Titanium Dioxide Nanocomposite Coating. <i>Nanoscale Research Letters</i> , 2018 , 13, 328	5	6
66	Highly Efficient Spintronic Terahertz Emitter Enabled by Metal-Dielectric Photonic Crystal. <i>Advanced Optical Materials</i> , 2018 , 6, 1800965	8.1	36
65	Vertically Emitting Indium Phosphide Nanowire Lasers. <i>Nano Letters</i> , 2018 , 18, 3414-3420	11.5	25

64	Avalanche Ruggedness of GaN p-i-n Diodes Grown on Sapphire Substrate. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018 , 215, 1800069	1.6	6
63	Photodetectors: Solvent-Based Soft-Patterning of Graphene Lateral Heterostructures for Broadband High-Speed Metal Semiconductor Metal Photodetectors (Adv. Mater. Technol. 2/2017). <i>Advanced Materials Technologies</i> , 2017 , 2,	6.8	2
62	Fine Control of the Electric Field Distribution in the Heterostructure Multiplication Region of AlGaN Avalanche Photodiodes. <i>IEEE Photonics Journal</i> , 2017 , 9, 1-7	1.8	4
61	A self-powered high-performance graphene/silicon ultraviolet photodetector with ultra-shallow junction: breaking the limit of silicon?. <i>Npj 2D Materials and Applications</i> , 2017 , 1,	8.8	144
60	4H-SiC Ultraviolet Avalanche Photodiodes With Small Gain Slope and Enhanced Fill Factor. <i>IEEE Photonics Journal</i> , 2017 , 9, 1-8	1.8	7
59	Solvent-Based Soft-Patterning of Graphene Lateral Heterostructures for Broadband High-Speed Metal Semiconductor Metal Photodetectors. <i>Advanced Materials Technologies</i> , 2017 , 2, 1600241	6.8	43
58	Solar-Blind Photodetector with High Avalanche Gains and Bias-Tunable Detecting Functionality Based on Metastable Phase β -GaO/ZnO Isotype Heterostructures. <i>ACS Applied Materials & Interfaces</i> , 2017 , 9, 36997-37005	9.5	106
57	A Terahertz Controlled-NOT Gate Based on Asymmetric Rotation of Polarization in Chiral Metamaterials. <i>Advanced Optical Materials</i> , 2017 , 5, 1700108	8.1	8
56	An Improved Design for Solar-Blind AlGaN Avalanche Photodiodes. <i>IEEE Photonics Journal</i> , 2017 , 9, 1-7	1.8	10
55	Abnormal mode splitting in photonic crystals micro-cavity containing highly dispersive metamaterials. <i>Journal of Optics (United Kingdom)</i> , 2017 , 19, 125101	1.7	
54	Tunneling-Hopping Transport Model for Reverse Leakage Current in InGaN/GaN Blue Light-Emitting Diodes. <i>IEEE Photonics Technology Letters</i> , 2017 , 29, 1447-1450	2.2	12
53	Photoluminescence Study of the Photoinduced Phase Separation in Mixed-Halide Hybrid Perovskite CHNHPb(BrI) Crystals Synthesized via a Solvothermal Method. <i>Scientific Reports</i> , 2017 , 7, 17695	4.9	13
52	Single Photon Counting Spatial Uniformity of 4H-SiC APD Characterized by SNOM-Based Mapping System. <i>IEEE Photonics Technology Letters</i> , 2017 , 29, 1603-1606	2.2	7
51	4H-SiC Avalanche Photodiode Linear Array Operating in Geiger Mode. <i>IEEE Photonics Journal</i> , 2017 , 9, 1-7	1.8	7
50	Analysis of Dark Count Mechanisms of 4H-SiC Ultraviolet Avalanche Photodiodes Working in Geiger Mode. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 4532-4539	2.9	11
49	4H-SiC SACM Avalanche Photodiode With Low Breakdown Voltage and High UV Detection Efficiency. <i>IEEE Photonics Journal</i> , 2016 , 8, 1-7	1.8	12
48	High Fill-Factor 4H-SiC Avalanche Photodiodes With Partial Trench Isolation. <i>IEEE Photonics Technology Letters</i> , 2016 , 28, 2526-2528	2.2	16
47	High-Performance 4H-SiC p-i-n Ultraviolet Photodiode With p Layer Formed by Al Implantation. <i>IEEE Photonics Technology Letters</i> , 2016 , 28, 1189-1192	2.2	11

46	Developing LED UV fluorescence sensors for online monitoring DOM and predicting DBPs formation potential during water treatment. <i>Water Research</i> , 2016 , 93, 1-9	12.5	69
45	A method of applying compressive pre-stress to AlGaN barrier in AlGaN/GaN heterostructures by depositing an additional thermally mismatched dielectric. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016 , 213, 2474-2478	1.6	1
44	Improved Schottky contacts to InGaN alloys by a photoelectrochemical treatment. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016 , 213, 1034-1038	1.6	
43	High-voltage photoconductive semiconductor switches fabricated on semi-insulating HVPE GaN:Fe template. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2016 , 13, 374-377		4
42	Electrically tunable terahertz metamaterials with embedded large-area transparent thin-film transistor arrays. <i>Scientific Reports</i> , 2016 , 6, 23486	4.9	12
41	High-Quality Crystal Growth and Characteristics of AlGaN-Based Solar-Blind Distributed Bragg Reflectors with a Tri-layer Period Structure. <i>Scientific Reports</i> , 2016 , 6, 29571	4.9	6
40	Polarization-independent split bullseye antennas for infrared nano-photodetectors. <i>Scientific Reports</i> , 2016 , 6, 39106	4.9	2
39	Highly selective and sensitive phosphate anion sensors based on AlGaN/GaN high electron mobility transistors functionalized by ion imprinted polymer. <i>Scientific Reports</i> , 2016 , 6, 27728	4.9	33
38	Frequency response and design consideration of GaN SAM avalanche photodiodes. <i>Applied Physics A: Materials Science and Processing</i> , 2016 , 122, 1	2.6	
37	Guided Bloch surface wave resonance for biosensor designs. <i>Journal of the Optical Society of America A: Optics and Image Science, and Vision</i> , 2016 , 33, 997-1003	1.8	14
36	Metasurface-enhanced optical Tamm states and related lasing effect. <i>Journal of the Optical Society of America B: Optical Physics</i> , 2015 , 32, 1624	1.7	4
35	Surface Acceptor-Like Trap Model for Gate Leakage Current Degradation in Lattice-Matched InAlN/GaN HEMTs. <i>IEEE Electron Device Letters</i> , 2015 , 36, 1281-1283	4.4	4
34	Metamaterials: Anomalous Terahertz Reflection and Scattering by Flexible and Conformal Coding Metamaterials (Advanced Optical Materials 10/2015). <i>Advanced Optical Materials</i> , 2015 , 3, 1373-1373	8.1	5
33	Anomalous Terahertz Reflection and Scattering by Flexible and Conformal Coding Metamaterials. <i>Advanced Optical Materials</i> , 2015 , 3, 1374-1380	8.1	131
32	Determination of Temperature-Dependent Stress State in Thin AlGaN Layer of AlGaN/GaN HEMT Heterostructures by Near-Resonant Raman Scattering. <i>Advances in Condensed Matter Physics</i> , 2015 , 2015, 1-6	1	
31	High-Temperature Single Photon Detection Performance of 4H-SiC Avalanche Photodiodes. <i>IEEE Photonics Technology Letters</i> , 2014 , 26, 1136-1138	2.2	44
30	High-Gain AlGaN Solar-Blind Avalanche Photodiodes. <i>IEEE Electron Device Letters</i> , 2014 , 35, 372-374	4.4	76
29	Reverse leakage current in AlGaN-based ultraviolet light-emitting diodes. <i>Science Bulletin</i> , 2014 , 59, 1276-1279		5

28	Sex- and season-dependent differences in telomere length and telomerase activity in the leaves of ash and willow. <i>SpringerPlus</i> , 2014 , 3, 163		4
27	Significant Performance Improvement in AlGaIn Solar-Blind Avalanche Photodiodes by Exploiting the Built-In Polarization Electric Field. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2014 , 20, 187-192	3.8	23
26	Plasmonic Fraunhofer-wavelength narrow-band filter based on calcium film. <i>Optik</i> , 2014 , 125, 3355-3357	2.5	
25	Large-Swing a-IGZO Inverter With a Depletion Load Induced by Laser Annealing. <i>IEEE Electron Device Letters</i> , 2014 , 35, 1034-1036	4.4	24
24	Energy Consumption Analysis of Sludge Transport Pipeline System Based on GA-DE Hybrid Algorithm. <i>Journal of Chemical Engineering of Japan</i> , 2014 , 47, 621-627	0.8	3
23	Solar-blind ultraviolet AlInN/AlGaIn distributed Bragg reflectors. <i>Applied Physics Letters</i> , 2013 , 102, 242112	14	15
22	A flexible wideband bandpass terahertz filter using multi-layer metamaterials. <i>Applied Physics B: Lasers and Optics</i> , 2013 , 113, 285-290	1.9	25
21	The Fano-type transmission and field enhancement in heterostructures composed of epsilon-near-zero materials and truncated photonic crystals. <i>Applied Physics Letters</i> , 2013 , 103, 201902	3.4	5
20	Exploitation of Polarization in Back-Illuminated AlGaIn Avalanche Photodiodes. <i>IEEE Photonics Technology Letters</i> , 2013 , 25, 1510-1513	2.2	23
19	High Quantum Efficiency GaN-Based p-i-n Ultraviolet Photodetectors Prepared on Patterned Sapphire Substrates. <i>IEEE Photonics Technology Letters</i> , 2013 , 25, 652-654	2.2	32
18	High-efficiency nonlinear platform with usage of metallic nonlinear susceptibility. <i>Optics Letters</i> , 2013 , 38, 1283-5	3	4
17	Light tunneling effect tuned by a meta-interface with electromagnetically-induced-transparency-like properties. <i>Applied Physics Letters</i> , 2013 , 102, 251908	3.4	7
16	Optical Tamm states in hetero-structures with highly dispersive planar plasmonic metamaterials. <i>Applied Physics Letters</i> , 2013 , 102, 111909	3.4	16
15	Improvements in Microstructure and Leakage Current of High-In-Content InGaIn p-i-n Structure by Annealing. <i>IEEE Photonics Technology Letters</i> , 2012 , 24, 1478-1480	2.2	3
14	Ultra-Low Dark Current AlGaIn-Based Solar-Blind Metal-Semiconductor-Metal Photodetectors for High-Temperature Applications. <i>IEEE Sensors Journal</i> , 2012 , 12, 2086-2090	4	57
13	Bias-Selective Dual-Operation-Mode Ultraviolet Schottky-Barrier Photodetectors Fabricated on High-Resistivity Homoepitaxial GaN. <i>IEEE Photonics Technology Letters</i> , 2012 , 24, 2203-2205	2.2	7
12	Enhanced nonlinear optical response of a planar thick metal film combined with a truncated photonic crystal. <i>Optics Communications</i> , 2012 , 285, 5416-5419	2	5
11	Electrical instability of amorphous indium-gallium-zinc oxide thin film transistors under monochromatic light illumination. <i>Applied Physics Letters</i> , 2012 , 100, 243505	3.4	66

10	Characteristics of polarization-doped N-face III-nitride light-emitting diodes. <i>Applied Physics Letters</i> , 2012 , 100, 073507	3.4	12
9	GaN MSM photodetectors fabricated on bulk GaN with low dark-current and high UV/visible rejection ratio. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 2473-2475		9
8	Field-dependent carrier trapping induced kink effect in AlGa _N /Ga _N high electron mobility transistors. <i>Applied Physics Letters</i> , 2011 , 98, 173508	3.4	29
7	Fabrication of blue and green non-polar InGa _N /Ga _N multiple quantum well light-emitting diodes on LiAlO ₂ (100) substrates. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2010 , 207, 1404-1406 ^{1.6}		3
6	InGa _N /Ga _N multi-quantum-well-based light-emitting and photodetective dual-functional devices. <i>Frontiers of Optoelectronics in China</i> , 2009 , 2, 442-445		0
5	Structural and optical characteristics of Al _x Ga _{1-x} N/AlN superlattice. <i>Science in China Series D: Earth Sciences</i> , 2009 , 52, 332-335		1
4	Modification of the valence band structures of polar and nonpolar plane wurtzite-GaN by anisotropic strain. <i>Journal of Applied Physics</i> , 2009 , 106, 023714	2.5	22
3	Developing a Miniaturized Spectrophotometer Using 235 and 275 nm UVC-LEDs for Fast Detection of Nitrate in Natural Water and Wastewater Effluents. <i>ACS ES&T Water</i> ,		1
2	Electrically tunable terahertz metamaterials with embedded large-area transparent thin-film transistor arrays		1
1	An experimental study on the pretreatment of lignite upgrading wastewater using the Fenton oxidation method. <i>Chemical Papers</i> ,1	1.9	